

WHAT IS CLAIMED IS

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1. A stacked semiconductor device,
comprising:

- 10 a first semiconductor device unit
comprising a first wiring substrate, at least one
semiconductor device mounted on said first wiring
substrate, and an external connection terminal,
a second wiring substrate that is prepared
below said first semiconductor device unit,
a second semiconductor device unit
15 comprising at least one semiconductor device that is
mounted on said second wiring substrate, and a
connection electrode formed on a surface of said
second wiring substrate, said surface facing said
first semiconductor device unit,
20 a third wiring substrate, comprising a
circuit board of said third wiring substrate
arranged between said first semiconductor device
unit and said second semiconductor device unit, a
first conductive member for electrically connecting
25 said circuit board and said connection electrode, a
second conductive member that is formed
corresponding to a form position of said external
connection terminal, said second conductive member
being electrically connected to said external
30 connection terminal, and a third conductive member
for electrically connecting said first conductive
member and said second conductive member.

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2. The stacked semiconductor device as

claimed in claim 1, wherein said first conductive member is formed by a solder bump that is connected to said third conductive member, said solder bump penetrating said circuit board.

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3. The stacked semiconductor device as
10 claimed in claim 1, wherein:

a solder bump constitutes said first conductive member,

said second conductive member and said third conductive member are formed on a surface of
15 said third wiring substrate, said surface facing said second semiconductor device unit, and

said external connection terminal is electrically connected to said second conductive member through a through hole formed in said third
20 wiring substrate.

25 4. The stacked semiconductor device as claimed in claim 1, wherein:

said second conductive member and said third conductive member are formed on both surfaces of said third wiring substrate, one of said surfaces
30 facing said first semiconductor device unit, and the other facing said second semiconductor device unit, and

said third conductive member formed on said both surfaces is electrically connected to said
35 circuit board by a through-hole electrode formed by penetrating said circuit board.

5 5. The stacked semiconductor device as
claimed in claim 1, wherein two or more said first
semiconductor device units are stacked.

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6. The stacked semiconductor device as
claimed in claim 1, wherein two or more said second
semiconductor devices are stacked.

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7. The stacked semiconductor device as
claimed in claim 1, wherein said third wiring
20 substrate comprises a multilayered substrate.

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8. The stacked semiconductor device as
claimed in claim 1, wherein a passive component is
mounted on said third wiring substrate.

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9. The stacked semiconductor device as
claimed in claim 8, wherein
said third wiring substrate comprises a
35 multilayered substrate, and said passive component
is formed inside said multilayered substrate.